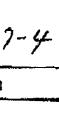
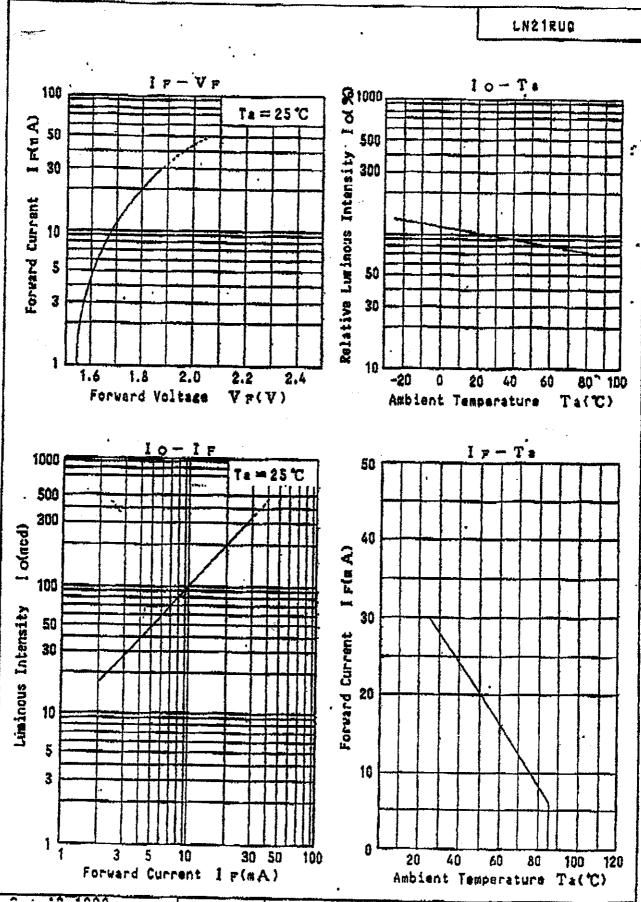
فتحدث والمالية والمالية والمالية والمالية					
	SEMICONDUCT	OR PI	UGOF	CT	
	L N 2 1 R	υQ			
TYPE	Red Light Emitting	Diode	•		
MATERIAL	GaAlAs				
APPLICATION	Indicators ·				
OUTLINE					
CONNECTION					
ABSOLUTE	Pa *IFP IFOC V	R T	Topr Tata		
MAXIMUM	70 150 30	3 -25	~ +85	-30~	100
RATINGS	v An An Va	• *	<u>.</u>	ン	
	Te=25±3°C				
· T	st Specific	ati	ОД		
	Condition	Tus.	Li	nit	Unit
	Condicton	Тур	Min	Max	
V F	IF=20mA	1.8	·	2.6	٧
IR	VR= 3 V			100	ДA
.10	IF=20mA oc	500	120		RCd
λρ	IF=20mA DC	660			na.
. Δλ	IF=20mA DC	20			n.
	•		· · · · · · · · · · · · · · · · · · ·		

^{. *1} The condition of IFP is duty 10%, Pulse width issec.

^{*2} Lead material and surface treatment : Pe type + solder dipping





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P.04 **ELECTROMARK**

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LN21RUG RELIABILITY TEST DATA

TEST CONDITION AND RESULT

TEST ITEM	TEST CONDITION	RESULTS	
Consecutive operating life test	test IF DC max, Ta=25°C, t=1,000h		
High temperature storage life test	Tate max, t=1,000h .	0/100	
Low temperature storage life test	Tate min. t=1,000h	0/100	
Tropical life test	Ta=60°C, RH≥90%, t=1.000h	0/100	
Soldering test	Ta=230±5℃, t=5mc, lcycle, flux	0/60	
Soldering heat test	Ta=280 ±5°C, t=10sec, lcycle	0/100	
Temperature cycle test (gaseous phase)	Tetrain ~ 25°C ~ Tetraex ~ 25°C (30min Smin Smin) × 10 cycles	0/100	
Thermal shock test (liquid phase)	Tute max ~ 0°C (5min 5min) × 10 cycles	0/100	
Fall test	Haple Wood h=75cm, 3 cycles	0/50	
Germinal strength cest	V=1Kg, t=30sec	0/50	
id Bending W=0.5Kg. 2 cycles		0/50	

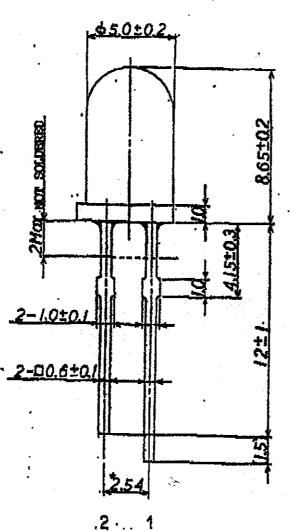
ITEX	SYMBOL"	- CONDITIONS	LIHIT	UNIT	
Forward Voltage	VP	Same as the specification	Upper×1-2	· V	
Reverse Leakage Current	IR	Same as the specification	Upper×2.0	μÅ	
Luminous Intensity	Io	Same as the specification	Min × 70	%	

^{*} note: Operating Life Stability 2 50%

^{*} Assurance for LED

[·]Assurance for LEO wihtin each condition is mentioned above.

LN21RUQ



1 : Anode

2: Cathode

" Lead wire dimension. (The bottom of lead)

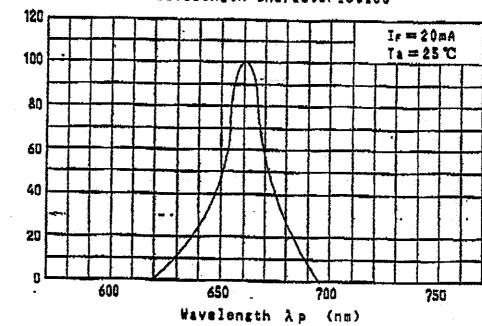
ELECTROMARK P. 02

MON-85-1835 18:22 FROM PIC Semiconductor MJ

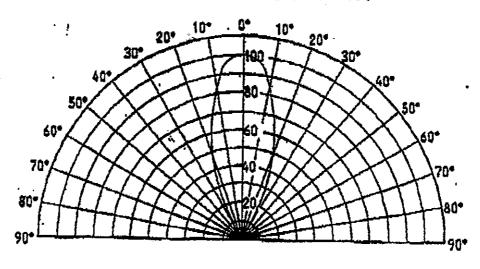
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LN21RUQ

Relative Luminous Intensity Wavelength Characteristics



Directive Characteristics



Relative Luminous Intensity (96)

" 3. Electro-optical characteristics (Note 2)

			·						
Parameter		Symbol		Condition	Hin .	Тур	Max	U	
Threshold curren	t	Ith		СМ	20	40	65	-	
Operating curren	t :	" lop		Po=3mw	30	50	75		
Operating voltage	2	Vop		Po=3mH	1-	1.75	2.5	<u> </u> 	
Havelength		ً کر	(Note 3)	Po=3mH	775	790	810	<u> </u>	
Radiation	Parallel	9 []	(Note 4)	Po=3mH	8	11	16		
angle	Perpendicular	9	(Note 4)	Po=3mW	20	33	45		
Differential eff	iciency	7	(Note 3)	2mH/(1(3mH)-!(1mH))	0.1	0.4	0.7		
PIN dark current		Id		Vr (PIN) = 30 V		_	0.1		
PIN photo-current	Marie Property (Control of Control of Contro	[p		Po=3mW Vr (P1N)=5V	0.2	0.6	1.0		
Emission point	X direction	8 <i>x</i>		Po=3mW	_	_	±2		
angle accuracy	Y direction	8у		Po=3mH			±3		
Oscillation mode			Sin	gle transverse mode				_	

(Note 2) Initial value
(Note 3) Sampling inspection by lot
(Note 4) Angle of 50% peak intensity (FHIIN)

单击下面可查看定价,库存,交付和生命周期等信息

>>Panasonic(松下)